

Silicon PNP Power Transistors

2SB696

DESCRIPTION

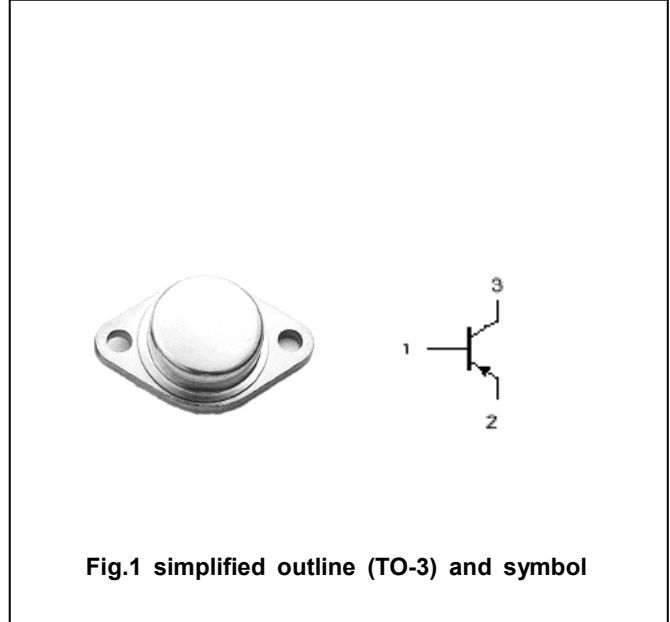
- With TO-3 package
- High power dissipation

APPLICATIONS

- Power amplifier applications
- Recommended for high-power high-fidelity audio frequency amplifier output stage

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-120	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-8	A
P_C	Collector power dissipation	$T_C = 25 \square$	80	W
T_j	Junction temperature		150	\square
T_{stg}	Storage temperature		-40~150	\square

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -50\text{mA}; I_B = 0$	-120			V
$V_{(BR)CBO}$	Collector-emitter breakdown voltage	$I_C = -5\text{mA}; I_E = 0$	-150			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = -5\text{mA}; I_C = 0$	-6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = -4\text{A}; I_B = -0.4\text{A}$			-2.5	V
V_{BE}	Base-emitter on voltage	$I_C = -1\text{A}; V_{CE} = -5\text{V}$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB} = -80\text{V}; I_E = 0$			-0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB} = -4\text{V}; I_C = 0$			-0.1	mA
h_{FE-1}	DC current gain	$I_C = -1\text{A}; V_{CE} = -5\text{V}$	40		320	
h_{FE-2}	DC current gain	$I_C = -4\text{A}; V_{CE} = -5\text{V}$	20			
f_T	Transition frequency	$I_C = -1\text{A}; V_{CE} = -5\text{V}$		15		MHz

◆ h_{FE-1} Classifications

C	D	E	F
40-80	60-120	100-200	160-320

PACKAGE OUTLINE

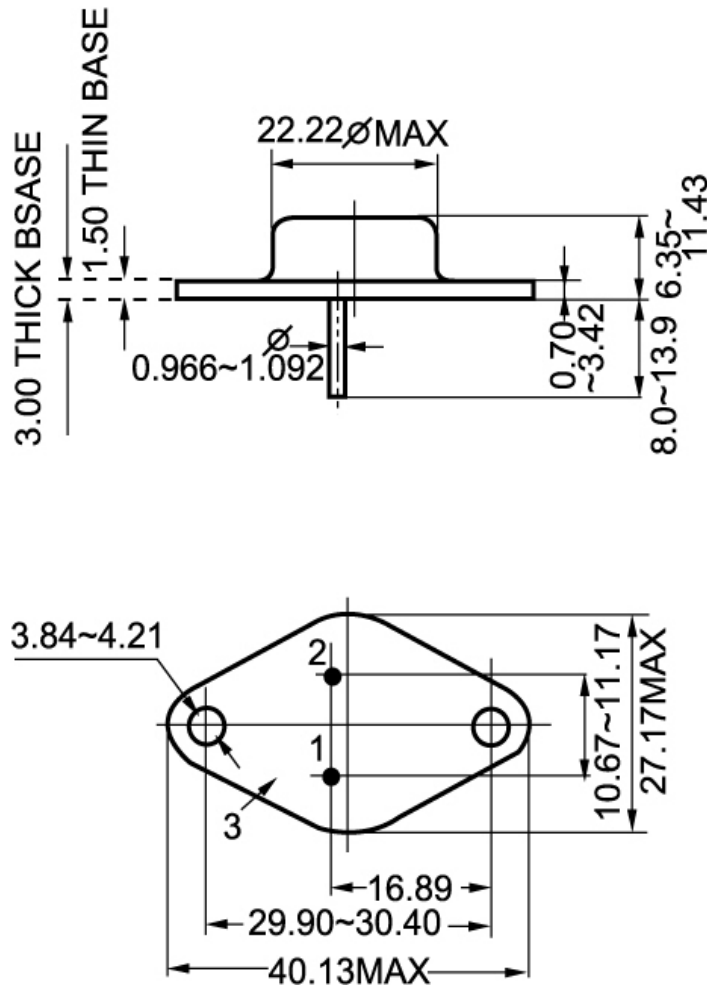


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)